MJE371G

Plastic Medium-Power PNP Silicon Transistor

This device is designed for use in general-purpose amplifier and switching circuits. Recommended for use in 5 to 20 Watt audio amplifiers utilizing complementary symmetry circuitry.

Features

- High DC Current Gain
- MJE371 is Complementary to NPN MJE521
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CB}	40	Vdc
Emitter-Base Voltage	V _{EB}	4.0	Vdc
Collector Current – Continuous	Ic	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current – Continuous	I _B	2.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 320	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.12	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I _C = 100 mAdc, I _B = 0) (Note 1)	V _{CEO(sus)}	40	_	Vdc
Collector–Base Cutoff Current (V _{CB} = 40 Vdc, I _E = 0)	I _{CBO}	_	100	μAdc
Emitter–Base Cutoff Current (V _{EB} = 4.0 Vdc, I _C = 0)	I _{EBO}	_	100	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 1)	h _{FE}			_
$(I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc})$. –	40	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

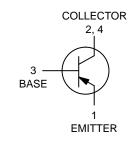
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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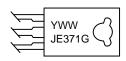
http://onsemi.com

4 AMPERES POWER TRANSISTOR PNP SILICON 40 VOLTS, 40 WATTS





MARKING DIAGRAM



Y = Year

WW = Work Week

JE371 = Device Code

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE371G	TO-225 (Pb-Free)	500 Units / Box

MJE371G

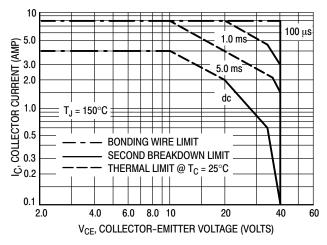


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less then the limitations imposed by second breakdown.

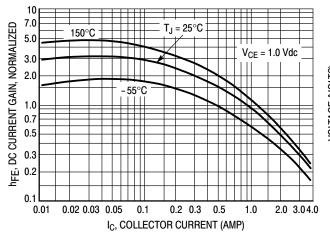


Figure 2. DC Current Gain

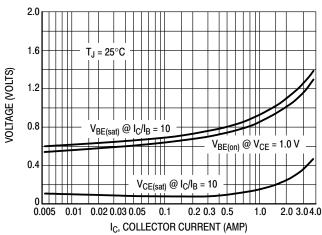


Figure 3. "On" Voltage

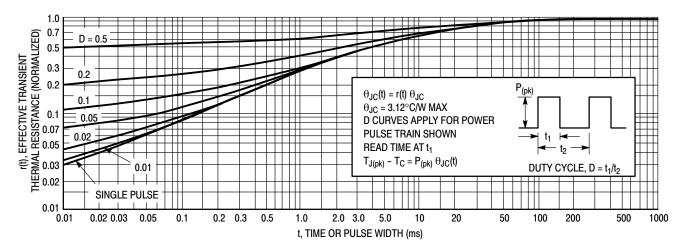
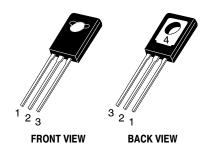


Figure 4. Thermal Response

MECHANICAL CASE OUTLINE

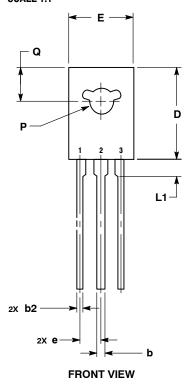


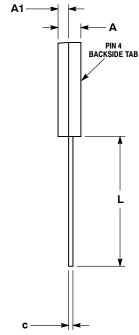


TO-225 CASE 77-09 **ISSUE AD**

DATE 25 MAR 2015

SCALE 1:1



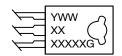


SIDE VIEW

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.40	3.00			
A1	1.00	1.50			
b	0.60	0.90			
b2	0.51	0.88			
C	0.39	0.63			
D	10.60	11.10			
E	7.40	7.80			
е	2.04	2.54			
L	14.50	16.63			
L1	1.27	2.54			
P	2.90	3.30			
Q	3.80	4.20			

GENERIC MARKING DIAGRAM*



= Year ww = Work Week

XXXXX = Device Code = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

,	EMITTER COLLECTOR BASE	,	CATHODE ANODE GATE	STYLE 3: PIN 1. 2., 4. 3.	COLLECTOR	,	ANODE 1 ANODE 2 GATE	STYLE 5: PIN 1. 2., 4. 3.	
STYLE 6: PIN 1.	CATHODE	STYLE 7: PIN 1.	MT 1	STYLE 8: PIN 1.	SOURCE	STYLE 9: PIN 1.	GATE	STYLE 10: PIN 1.	SOURC

YLE 6:		STYLE 7:		STYLE 8:		STYLE 9:		STYLE 10:	
PIN 1.	CATHODE	PIN 1.	MT 1	PIN 1.	SOURCE	PIN 1.	GATE	PIN 1.	SOURCE
2., 4.	GATE	2., 4.	GATE	2., 4.	GATE	2., 4.	DRAIN	2., 4.	DRAIN
3.	ANODE	3.	MT 2	3.	DRAIN	3.	SOURCE	3.	GATE

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